Lonten N-channel 100V, 53A, 8mΩ Power MOSFET

Description

These N-Channel enhancement mode power field effect transistors are using split gate trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and with stand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

Features

- 100V,53A, $R_{DS(on),max}$ =8mΩ@V_{GS} = 10V
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green device available

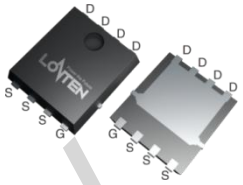
Applications

- Motor Drives
- UPS
- DC-DC Converter

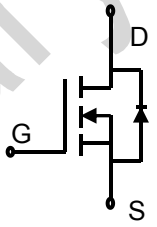
Product Summary

V_{DSS}	100V
$R_{DS(on),max}$@ V_{GS}=10V	8mΩ
I_D	53A

Pin Configuration



DFN5×6



N-Channel MOSFET

Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	100	V
Continuous drain current (T_C = 25°C)	I_D	53	A
(T_C = 100°C)		37	A
Pulsed drain current[1)]	I_{DM}	159	A
Gate-Source voltage	V_{GSS}	±20	V
Avalanche energy[2)]	E_{AS}	5	mJ
Power Dissipation	P_D	57	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.2	°C/W
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	55	°C/W

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Reel
LSGN10R080WB	DFN5X6	10R080WB	5000

Electrical Characteristics

T_J = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0 V, I_D=250uA	100	---	---	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	2	3	4	V
Drain-source leakage current	I_{DSS}	V_{DS}=100 V, V_{GS}=0V	---	---	1	μA
Gate leakage current, Forward	I_{GSSF}	V_{GS}=20 V, V_{DS}=0 V	---	---	100	nA
Gate leakage current, Reverse	I_{GSSR}	V_{GS}=-20 V, V_{DS}=0 V	---	---	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=13.5 A	---	5.9	8	mΩ
Forward transconductance	g_{fs}	V_{DS} =5V , I_D=20A	---	86.5	---	S
Dynamic characteristics						
Input capacitance	C_{iss}	V_{DS} = 50 V, V_{GS} = 0 V, F = 1MHz	---	3325	---	pF
Output capacitance	C_{oss}		---	608	---	
Reverse transfer capacitance	C_{rss}		---	23	---	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 50V,V_{GS}=10V, I_D = 13.5A R_G=3Ω	---	10.3	---	ns
Rise time	t_r		---	6.8	---	
Turn-off delay time	$t_{d(off)}$		---	44.5	---	
Fall time	t_f		---	7.8	---	
Gate charge characteristics						
Gate to source charge	Q_{gs}	V_{DS}=50V, I_D=20A, V_{GS}= 13.5 V	---	9.4	---	nC
Gate to drain charge	Q_{gd}		---	4.9	---	
Gate charge total	Q_g		---	54	---	
Drain-Source diode characteristics and Maximum Ratings						
Continuous Source Current	I_S		---	---	47.5	A
Pulsed Source Current[3)]	I_{SM}		---	---	142.5	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=13.5A, T_J=25℃	---	---	1.2	V
Reverse recovery time	t_{rr}	I_F=13.5A,dI_F/dt=100 A/μs	---	33	---	ns
Reverse recovery charge	Q_{rr}		---	150	---	nC

Notes:

1: Repetitive Rating: Pulse width limited by maximum junction temperature.

2: V_{DD}=50V, V_{GS}=10V, L=0.1mH, I_{AS}=10A, Starting T_J=25℃.

3: Pulse Test：Pulse Width ≤300μs, Duty Cycle≤2%.

Electrical Characteristics Diagrams

Figure 1. Typ. Output Characteristics

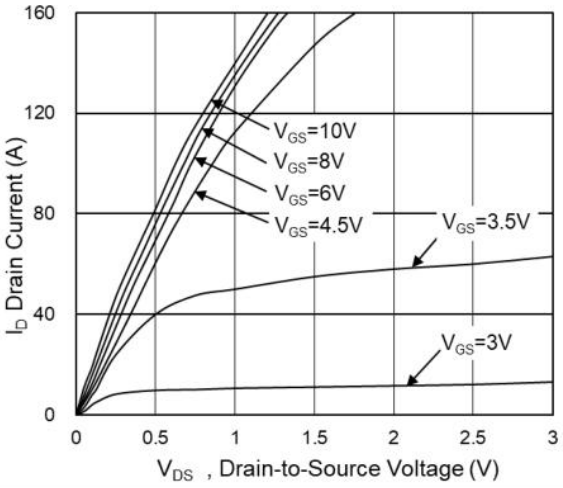


Figure 2. Transfer Characteristics

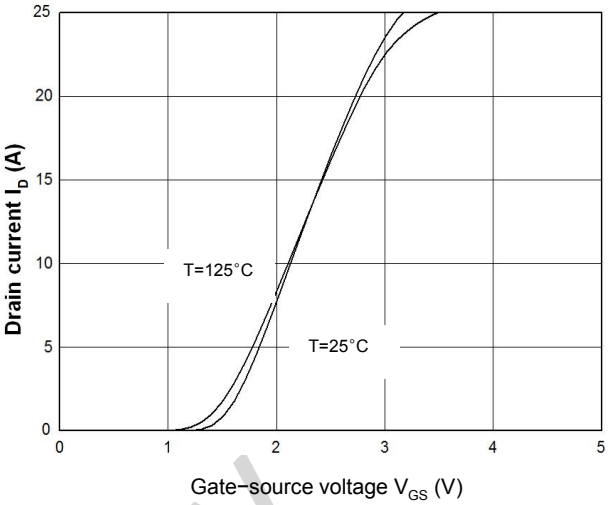


Figure 3. Capacitance Characteristics

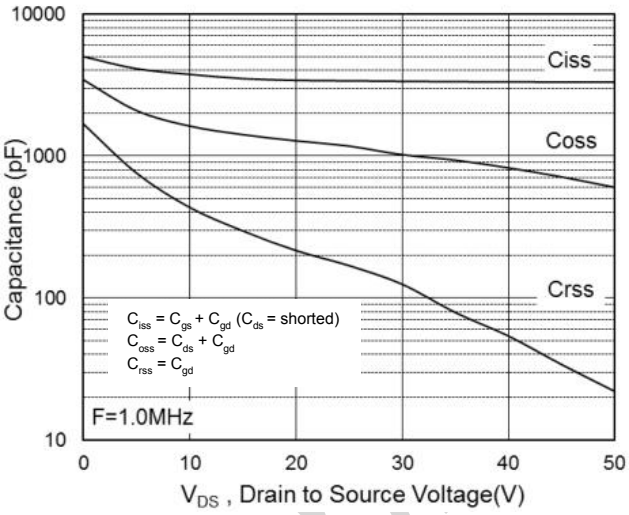


Figure 4. Gate Charge Waveform

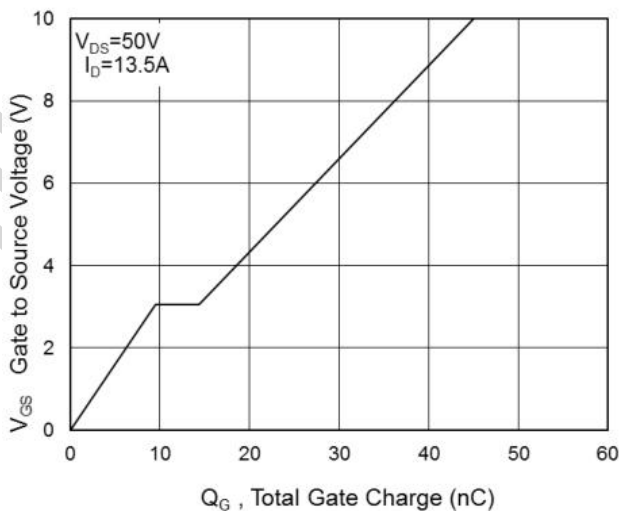


Figure 5. Body-Diode Characteristics

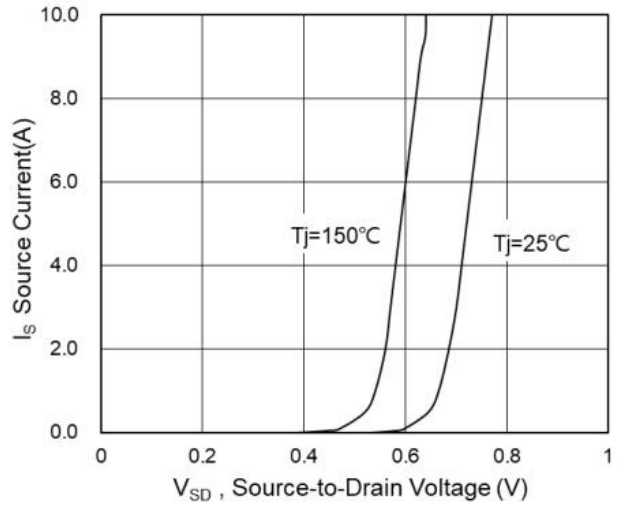


Figure 6. Rdson-Drain Current

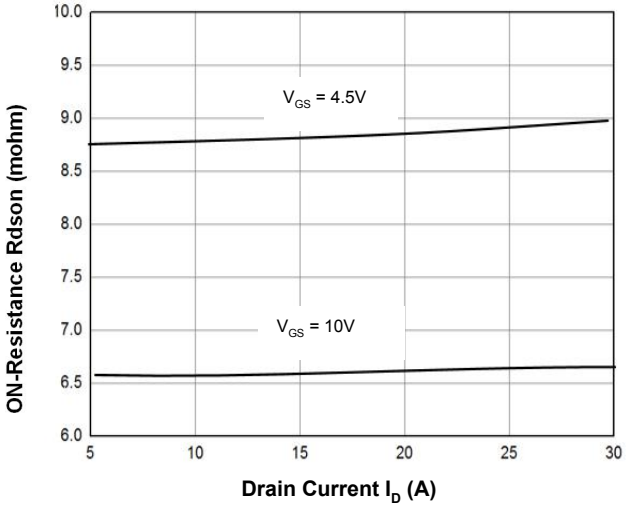


Figure 7. Rdson-Junction Temperature

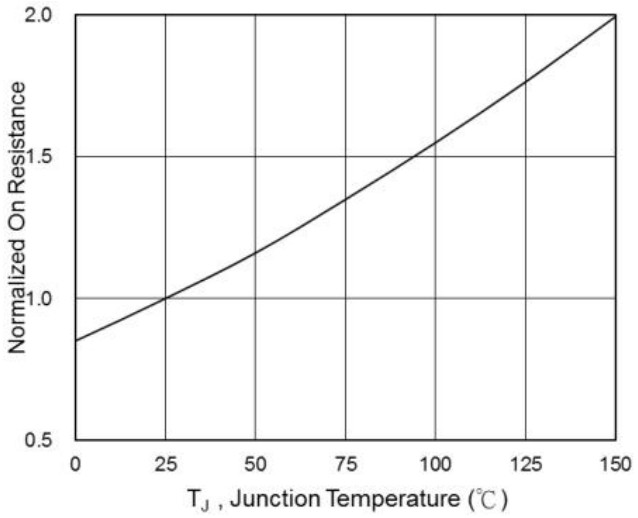


Figure 8. $V_{GS(th)}$-Junction Temperature

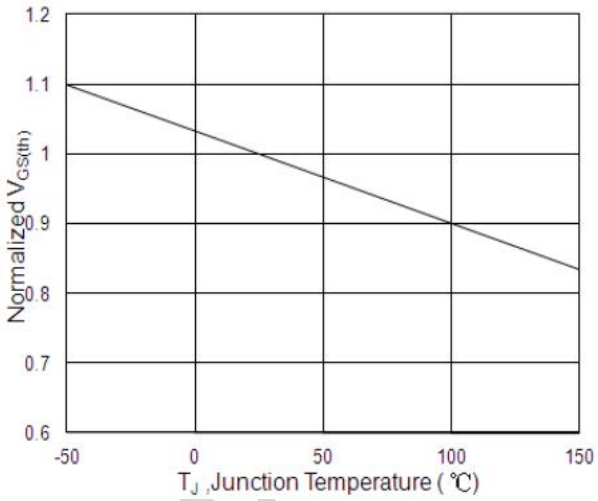


Figure 9. On-Resistance vs. Gate-to-Source voltage

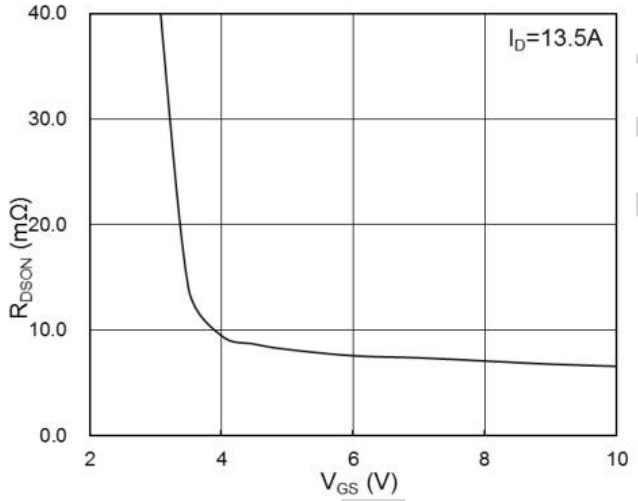


Figure 10: Safe Operating Area

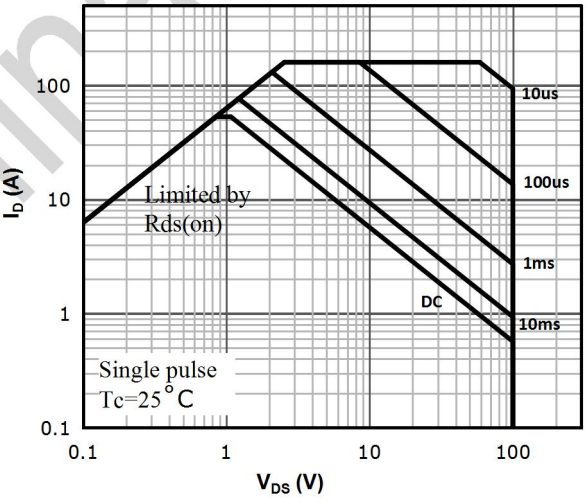
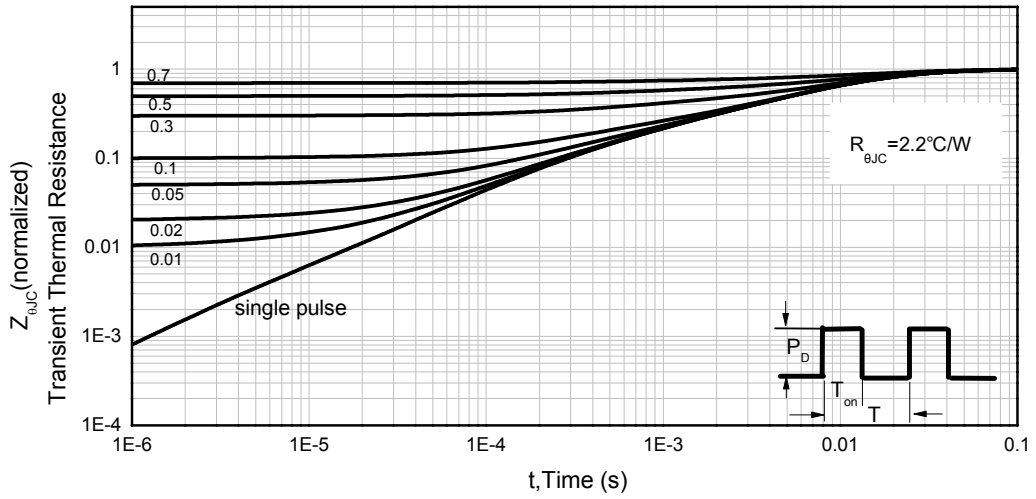
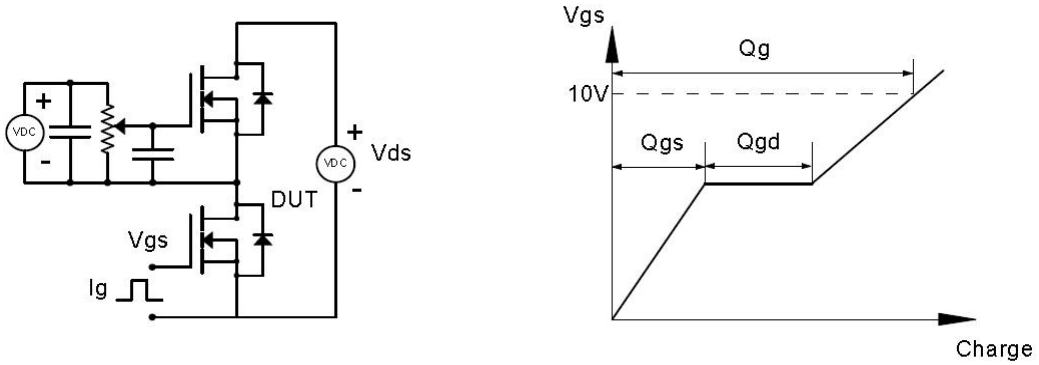


Figure 11. Normalized Maximum Transient Thermal Impedance (RthJC)

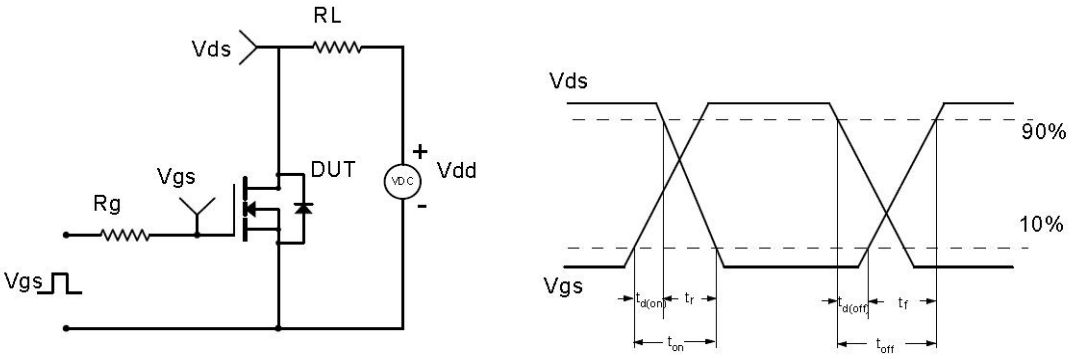


Test Circuit & Waveforms

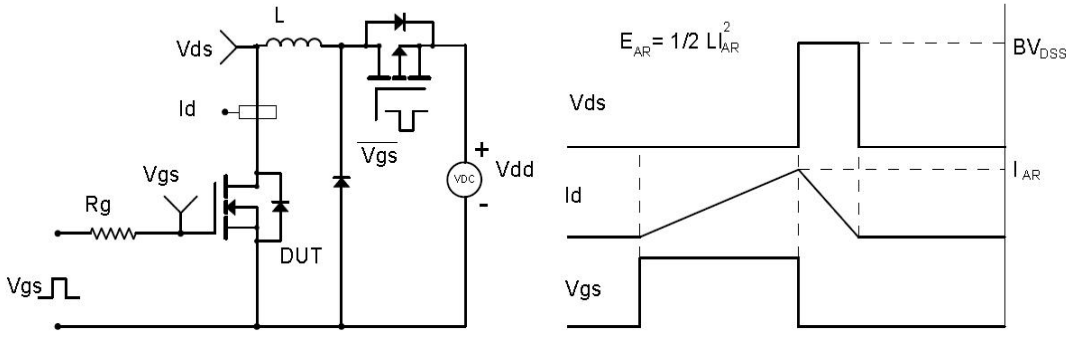
Gate Charge Test Circuit & Waveform



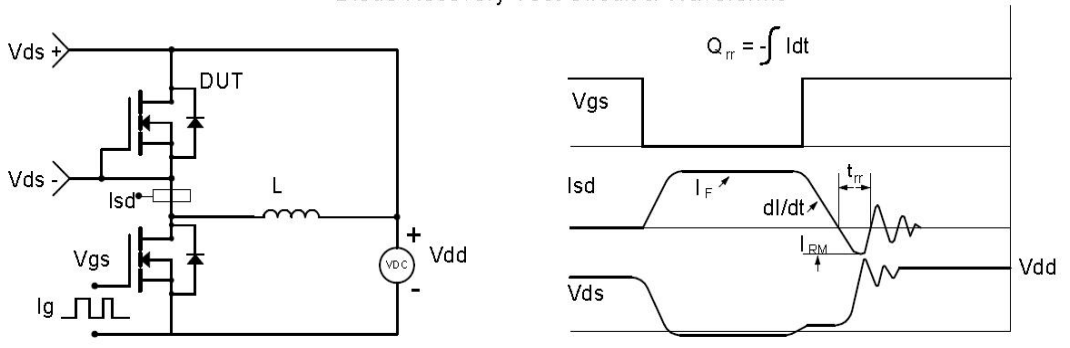
Resistive Switching Test Circuit & Waveforms



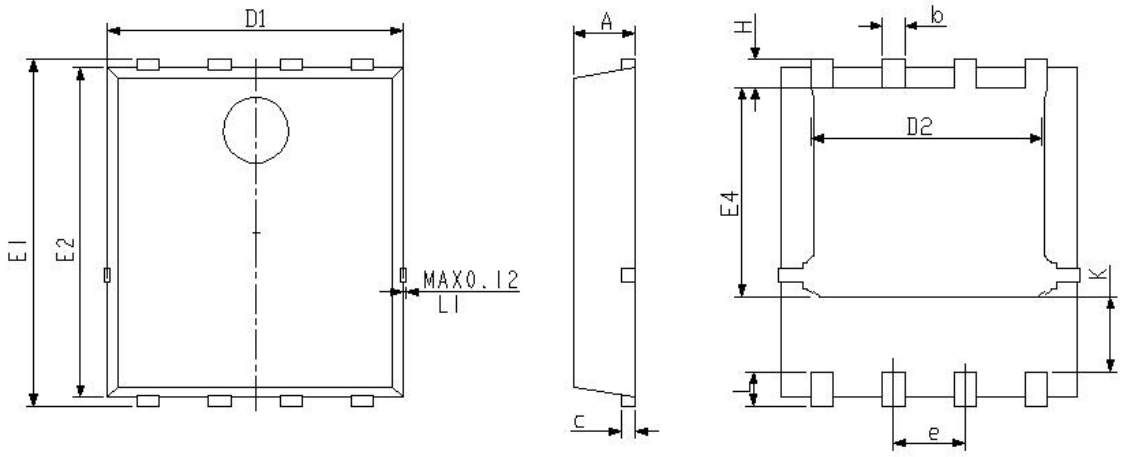
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Mechanical Dimensions for DFN5×6



DIMENSIONS IN MILLITMETERS			DIMENSIONS IN INCHES	
SYMBOL	MIN	MAX	MIN	MAX
A	0.85	1.20	0.033	0.047
b	0.30	0.51	0.012	0.020
c	0.15	0.35	0.006	0.014
D1	4.80	5.40	0.189	0.213
D2	3.70	4.55	0.146	0.179
E1	5.95	6.35	0.234	0.250
E2	5.45	6.06	0.215	0.239
E4	3.30	3.92	0.130	0.154
e	1.27BSC		0.05BSC	
L	0.3	0.71	0.012	0.028
H	0.38	0.71	0.015	0.028
K	1.15	1.45	0.045	0.057

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